

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: YOUNG HUN SEO

Application No.: Confirmation
No:
Filed: September 9, 2003 Group No.:
Examiner
For: METHOD FOR FORMING A SHALLOW TRENCH ISOLATION USING AIR GAP

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

APPLICATION DATA SHEET
37 C.F.R. § 1.76

BIBLIOGRAPHIC DATA

1. Applicant information

First applicant: YOUNG HUN SEO
Citizenship: Republic of KOREA
Residence: 532-104 Eunhamaeul, Jung 4-dong, Wonmi-gu, Bucheon-si, Gyeonggi-do, KOREA

2. Correspondence information

Correspondence for this application should be addressed as follows:

Customer No.: 00909

3. Application information

Title of Invention: METHOD FOR FORMING A SHALLOW TRENCH ISOLATION USING AIR GAP

Docket number assigned to this application: 021906-0305881

Suggested Classification: Class:
Subclass:
Technology Center to which subject matter is assigned:

Total number of drawing sheets: 4

Type of application:

Utility

Application is to be published. Suggested drawing figure for publication:

Secrecy order under § 5.2:

This application does not disclose subject matter of an application which is under a secrecy order pursuant to § 5.2.

4. Representative information

The following have a power of attorney or authorization of agent in this application:

Customer No.: 00909

5. Foreign priority information

Foreign priority is claimed for this application as follows:

Country: Republic of Korea
Application No.: 10-2002-0054202
Filing Date: September 9, 2002
Status: pending

6. Assignee information

The assignee(s) of this application is/are:

ANAM Semiconductor, Inc.
891-10 Daechi-dong, Gangnam-gu
Seoul,
KOREA
Extent of interest of assignee in application: 100%

Date: September 9, 2003

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